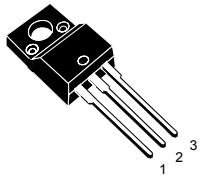
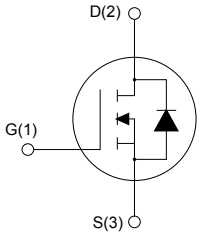
N-channel 600 V, 570 mΩ typ., 8 A FDmesh II Power MOSFET in a TO-220FP package



TO-220FP



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Features

Order code	V_{DS} at T_J max.	$R_{DS(on)}$ max.	I_D
STF10NM60ND	650 V	600 mΩ	8 A

- Fast-recovery body diode
- Low gate charge and input capacitance
- Low on-resistance $R_{DS(on)}$
- 100% avalanche tested
- High dv/dt ruggedness

Applications

- Switching applications

Description

This FDmesh II Power MOSFET with fast-recovery body diode is produced using MDmesh II technology. Utilizing a new strip-layout vertical structure, this device features low on-resistance and superior switching performance. It is ideal for bridge topologies and ZVS phase-shift converters.

Product status link
STF10NM60ND

Product summary	
Order code	STF10NM60ND
Marking	10NM60ND
Package	TO-220FP
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	600	V
V_{GS}	Gate-source voltage	±25	V
I_D	Drain current (continuous) at T_C = 25 °C	8	A
	Drain current (continuous) at T_C = 100 °C	5	
I_{DM}(1)	Drain current (pulsed)	32	A
P_{TOT}	Total power dissipation at T_C = 25 °C	25	W
dv/dt(2)	Peak diode recovery voltage slope	40	V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T_C = 25 °C)	2.5	kV
T_{stg}	Storage temperature range	-55 to 150	°C
T_J	Maximum operating junction temperature	150	°C

1. *Pulse width is limited by safe operating area.*
2. *I_{SD} ≤ 8 A, di/dt ≤ 400 A/µs, V_{DS} (peak) < $V_{(BR)DSS}$, V_{DD} = 80% $V_{(BR)DSS}$.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	5	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	62.5	°C/W

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AS}	Avalanche current, repetitive or non-repetitive (pulse width limited by T_J max.)	2.5	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, I_D = I_{AS}, V_{DD} = 50 V)	130	mJ

2 Electrical characteristics

T_C = 25 °C unless otherwise specified.

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	600			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 600 V			1	µA
		V_{GS} = 0 V, V_{DS} = 600 V, T_C = 125 °C(1)			100	µA
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 4 A		570	600	mΩ

1. *Specified by design, not tested in production.*

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 50 V, f = 1 MHz, V_{GS} = 0 V	-	577	-	pF
C_{oss}	Output capacitance		-	32.4	-	pF
C_{rss}	Reverse transfer capacitance		-	1.76	-	pF
$C_{oss\ eq.}$ (1)	Equivalent output capacitance	V_{GS} = 0 V, V_{DS} = 0 to 480 V	-	138	-	pF
R_G	Gate input resistance	f = 1 MHz, I_D=0 A	-	6	-	Ω
Q_g	Total gate charge	V_{DD} = 480 V, I_D = 8 A, V_{GS} = 0 to 10 V (see Figure 14. Test circuit for gate charge behavior)	-	20	-	nC
Q_{gs}	Gate-source charge		-	4.3	-	nC
Q_{gd}	Gate-drain charge		-	11.6	-	nC

1. *$C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.*

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 300 V, I_D = 4 A, R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	9.2	-	ns
t_r	Rise time		-	10	-	ns
$t_{d(off)}$	Turn-off delay time		-	32	-	ns
t_f	Fall time		-	9.8	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		8	A
I_{SDM}(1)	Source-drain current (pulsed)		-		32	A
V_{SD}(2)	Forward on voltage	I_{SD} = 8 A, V_{GS} = 0 V	-		1.5	V
t_{rr}	Reverse recovery time	I_{SD} = 8 A, di/dt = 100 A/µs, V_{DD} = 60 V (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	118		ns
Q_{rr}	Reverse recovery charge		-	680		nC
I_{RRM}	Reverse recovery current		-	11		A
t_{rr}	Reverse recovery time	I_{SD} = 8 A, di/dt = 100 A/µs, V_{DD} = 60 V, T_J = 150 °C (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	150		ns
Q_{rr}	Reverse recovery charge		-	918		nC
I_{RRM}	Reverse recovery current		-	12		A

1. *Pulse width is limited by safe operating area.*
2. *Pulsed: pulse duration = 300 µs, duty cycle 1.5%.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

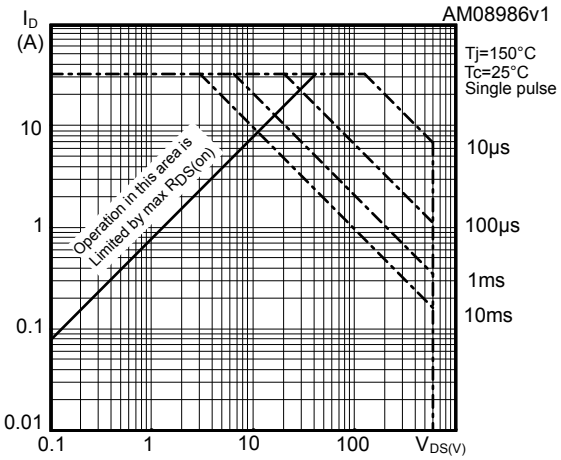


Figure 2. Normalized transient thermal impedance

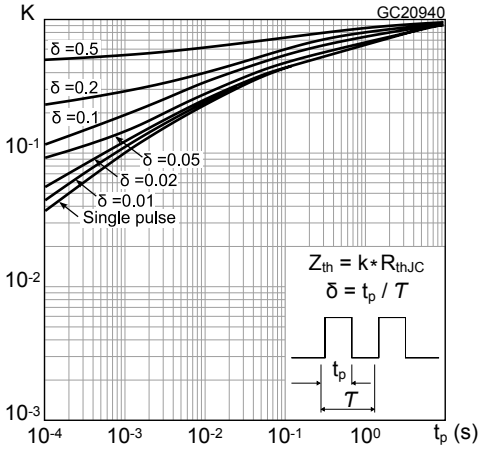


Figure 3. Typical output characteristics

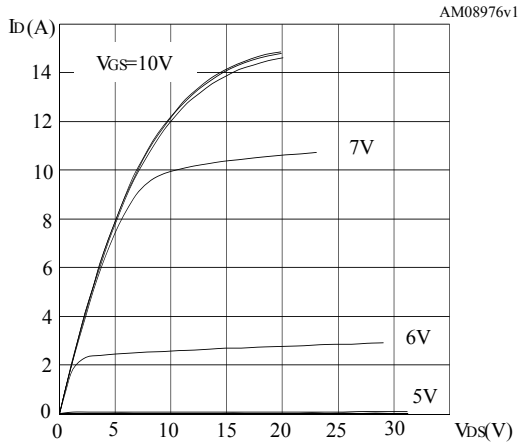


Figure 4. Typical transfer characteristics

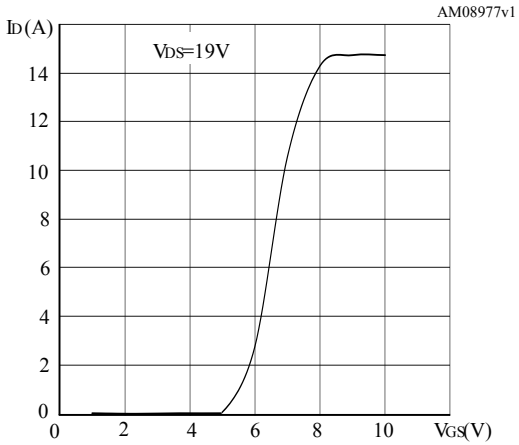


Figure 5. Normalized gate threshold vs temperature

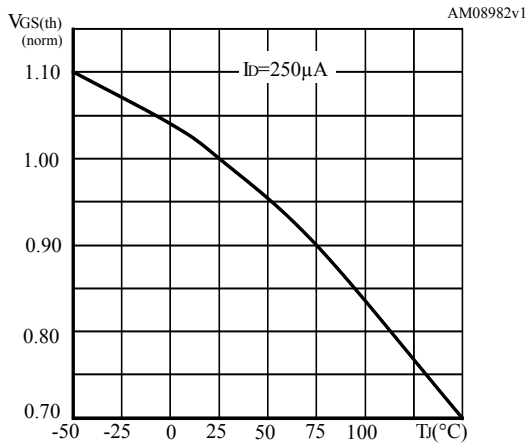


Figure 6. Normalized breakdown voltage vs temperature

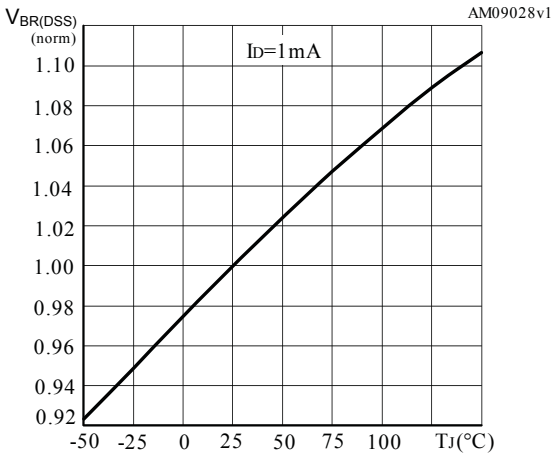


Figure 7. Typical drain-source on-resistance

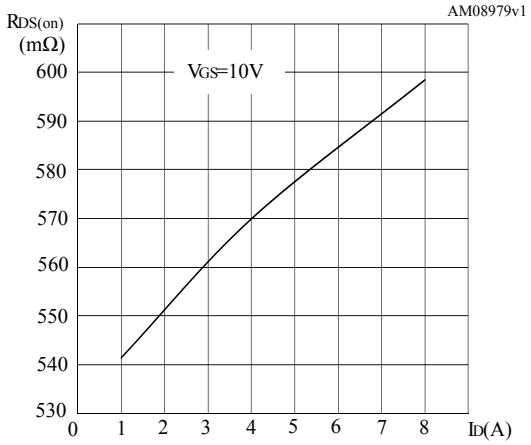


Figure 8. Normalized on-resistance vs temperature

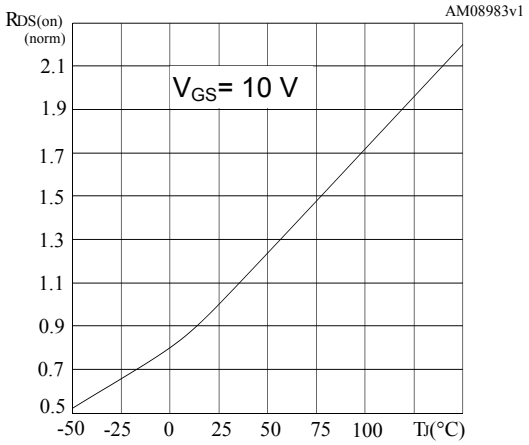


Figure 9. Typical gate charge characteristics

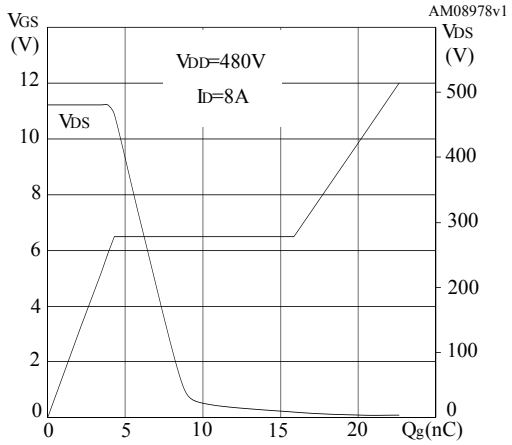


Figure 10. Typical capacitance characteristics

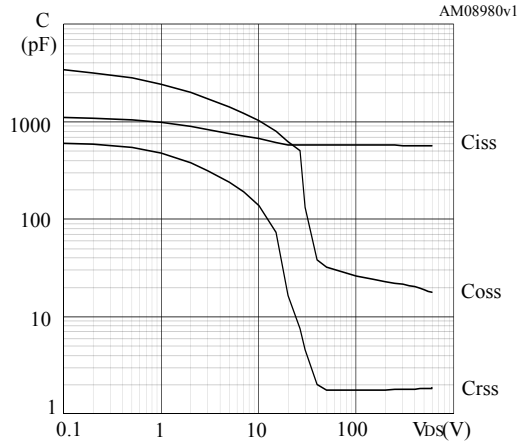


Figure 11. Typical output capacitance stored energy

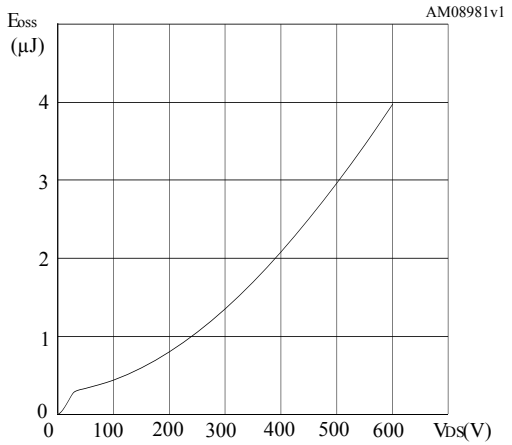
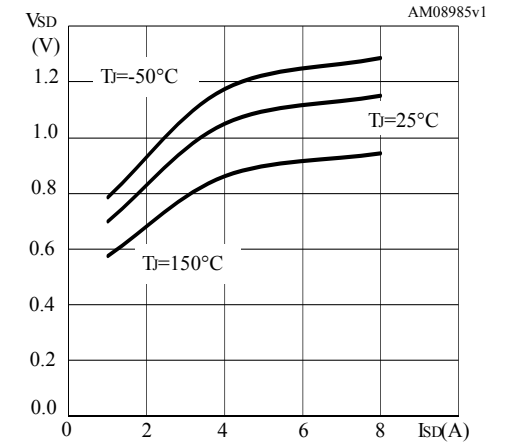


Figure 12. Typical reverse diode forward characteristics



3 Test circuits

Figure 13. Test circuit for resistive load switching times

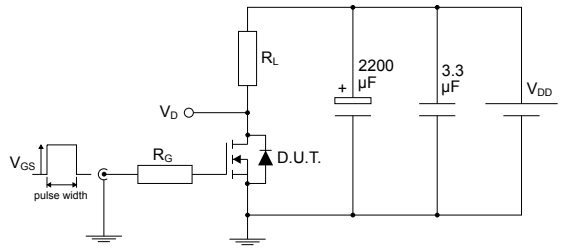


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Figure 14. Test circuit for gate charge behavior

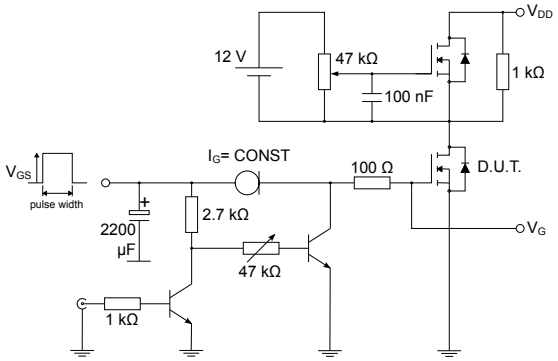

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Figure 15. Test circuit for inductive load switching and diode recovery times

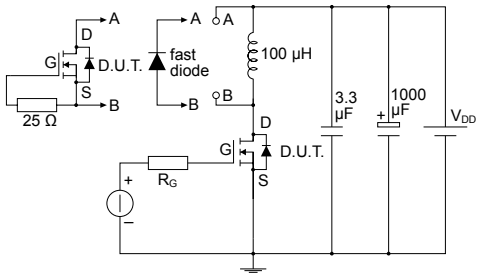

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Figure 16. Unclamped inductive load test circuit

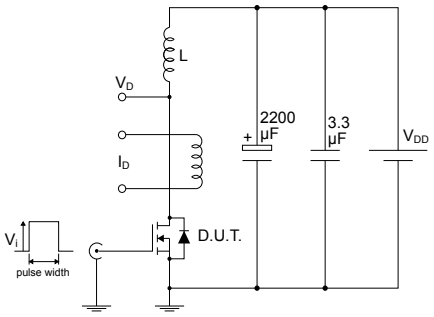

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Figure 17. Unclamped inductive waveform

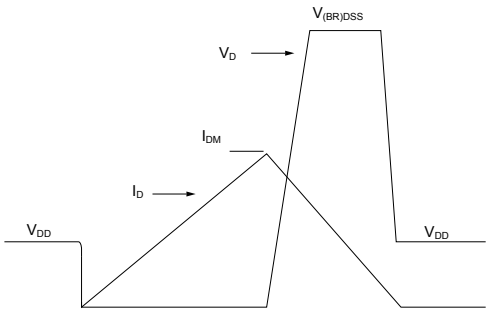

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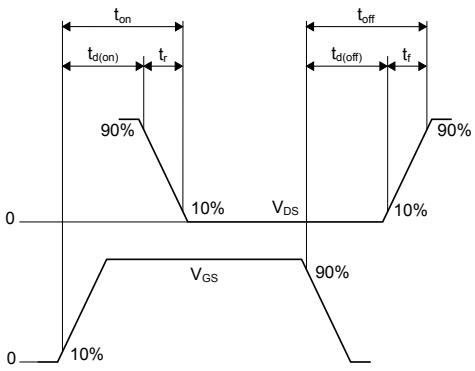
Figure 18. Switching time waveform



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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-220FP type B package information

Figure 19. TO-220FP type B package outline

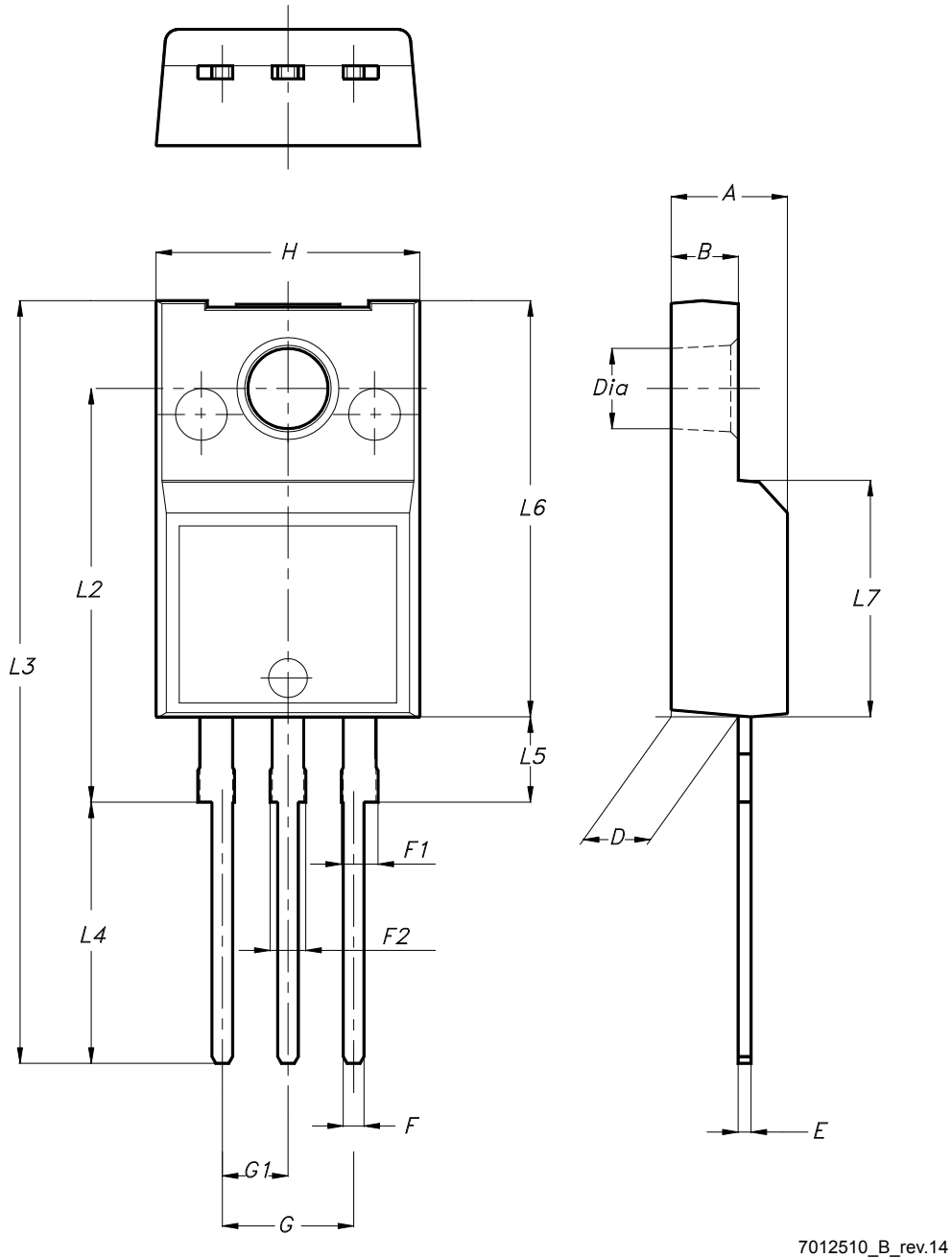

Table 8. **TO-220FP type B package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.70
F	0.75		1.00
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.20
G1	2.40		2.70
H	10.00		10.40
L2		16.00	
L3	28.60		30.60
L4	9.80		10.60
L5	2.90		3.60
L6	15.90		16.40
L7	9.00		9.30
Dia	3.00		3.20

Revision history

Table 9. **Document revision history**

Date	Revision	Changes
16-Jun-2023	1	First release. Part number previously included in datasheet DS7103.

Contents